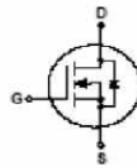


**MOSFET (N-Channel)****FEATURES**

- High density cell design for low $R_{DS(ON)}$
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability

**Marking: 702 ***

Note: " * " Represents the production batch,
production batch will vary over time.

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{DS}	Drain-Source voltage	60	V
I_D	Drain Current	115	mA
P_D	Power Dissipation	225	mW
R_{JA}	Thermal Resistance, junction to Ambient	556	$^\circ\text{C}/\text{W}$
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0 \text{ V}, I_D=10 \mu\text{A}$	60			V
Gate-Threshold Voltage	$V_{th(GS)}$	$V_{DS}=V_{GS}, I_D=250 \mu\text{A}$	1		2.5	
Gate-body Leakage	I_{GSS}	$V_{DS}=0 \text{ V}, V_{GS}=\pm 25 \text{ V}$			± 80	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60 \text{ V}, V_{GS}=0 \text{ V}$			80	nA
On-state Drain Current	$I_{D(ON)}$	$V_{GS}=10 \text{ V}, V_{DS}=7 \text{ V}$	500			mA
Drain-Source On-Resistance	$r_{DS(on)}$	$V_{GS}=10 \text{ V}, I_D=500 \text{ mA}$	1		7.5	Ω
		$V_{GS}=5 \text{ V}, I_D=50 \text{ mA}$	1		7.5	
Forward Trans conductance	g_{fs}	$V_{DS}=10 \text{ V}, I_D=200 \text{ mA}$	80		500	ms
Drain-source on-voltage	$V_{DS(on)}$	$V_{GS}=10 \text{ V}, I_D=500 \text{ mA}$	0.5		3.75	V
		$V_{GS}=5 \text{ V}, I_D=50 \text{ mA}$	0.05		0.375	V
Diode Forward Voltage	V_{SD}	$I_S=115 \text{ mA}, V_{GS}=0 \text{ V}$	0.55		1.2	V
Input Capacitance	C_{iss}	$V_{DS}=25 \text{ V}, V_{GS}=0 \text{ V}, f=1 \text{ MHz}$			50	pF
Output Capacitance	C_{oss}				25	
Reverse Transfer Capacitance	C_{rss}				5	

SWITCHING TIME

Turn-on Time	$t_{d(on)}$	$V_{DD}=25 \text{ V}, R_L=50 \Omega$			20	
Turn-off Time	$t_{d(off)}$	$I_D=500 \text{ mA}, V_{GEN}=10 \text{ V}$			40	ns



Typical Characteristics

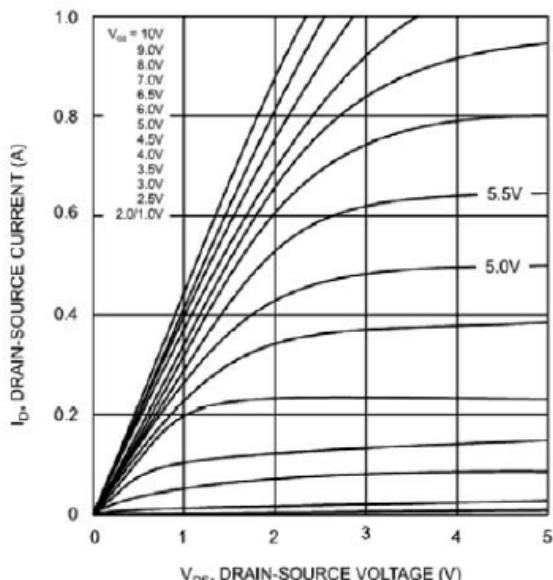


Fig. 1 On-Region Characteristics

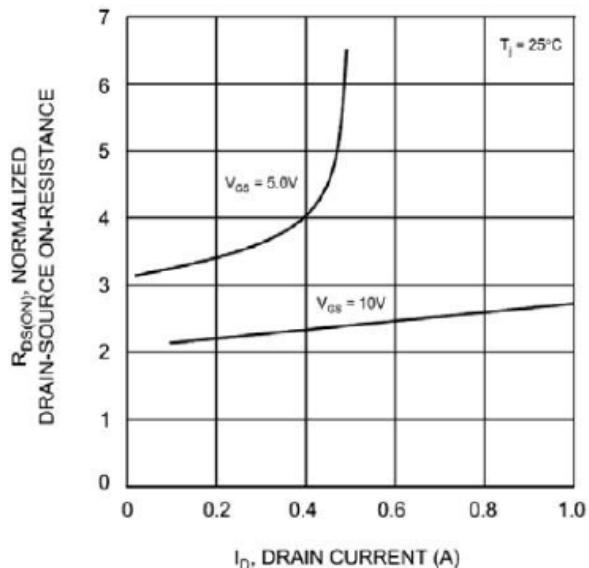


Fig. 2 On-Resistance vs Drain Current

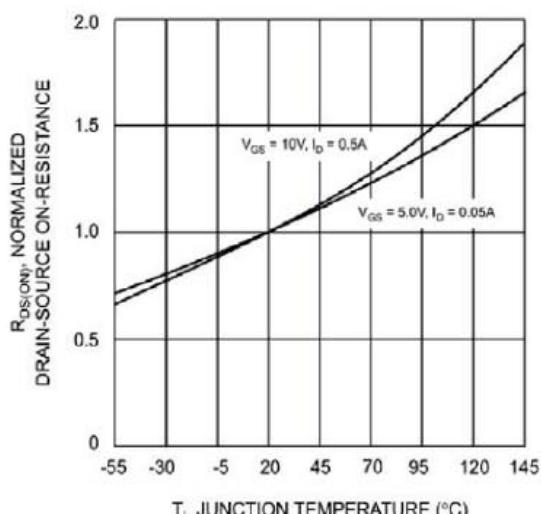


Fig. 3 On-Resistance vs Junction Temperature

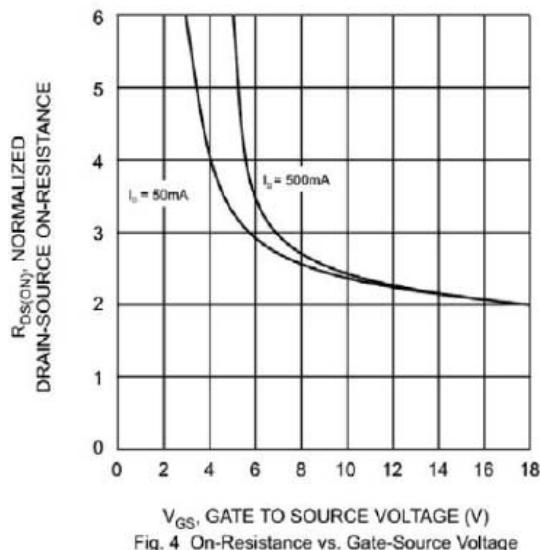


Fig. 4 On-Resistance vs. Gate-Source Voltage